

## Silicon NPN Power Transistors

2SD1279

## DESCRIPTION

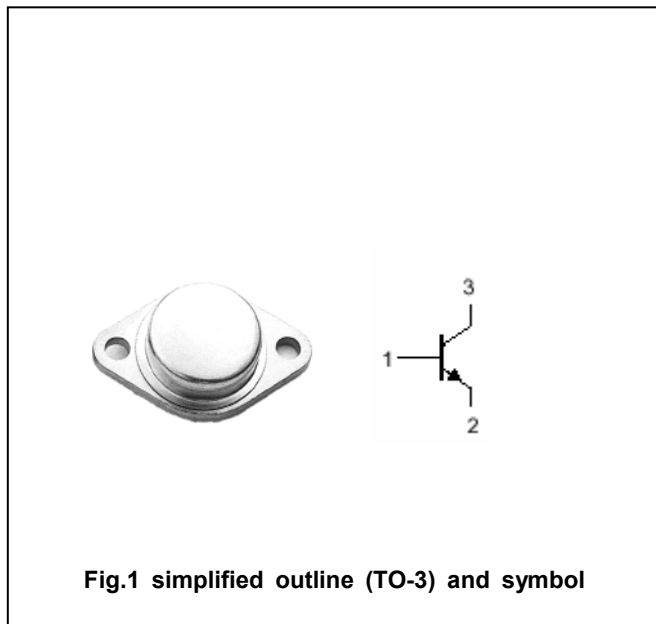
- With TO-3 package
- High voltage;high speed
- Low collector saturation voltage

## APPLICATIONS

- Color TV horizontal deflection output applications
- Switching regulator applications

## PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings( $T_a = \square$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	1400	V
$V_{CEO}$	Collector-emitter voltage	Open base	600	V
$V_{EBO}$	Emitter-base voltage	Open collector	5	V
$I_C$	Collector current		10	A
$I_B$	Base current		5	A
$P_C$	Collector power dissipation	$T_C = 25 \square$	50	W
$T_j$	Junction temperature		150	$\square$
$T_{stg}$	Storage temperature		-65~150	$\square$

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEQ(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =100mA ; I <sub>B</sub> =0	600			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =8A; I <sub>B</sub> =2A			5.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =8A; I <sub>B</sub> =2A			1.6	V
I <sub>CB0</sub>	Collector cut-off current	V <sub>CB</sub> =500V; I <sub>E</sub> =0			10	μA
I <sub>EB0</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			1.0	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =2A ; V <sub>CE</sub> =5V	8	22		
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.1A ; V <sub>CE</sub> =10V		3		MHz
C <sub>OB</sub>	Collector output capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> =10V; f=1MHz		165		pF
t <sub>f</sub>	Fall time	I <sub>CP</sub> =7A ; I <sub>B1(end)</sub> =1.5A			1.0	μs

PACKAGE OUTLINE



Fig.2 outline dimensions (unindicated tolerance:±0.1mm)